

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	757	(wafer die chip) with (opening vias hole) with (method process) with (dielectric insulative insulating) with (conductive conductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/19 15:14
L2	241	((wafer die chip) with (opening vias hole) with (method process) with (dielectric insulative insulating) with (conductive conductor)) and bump	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/19 15:14
L3	30	((((wafer die chip) with (opening vias hole) with (method process) with (dielectric insulative insulating) with (conductive conductor)) and bump) and (silicon adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/02/19 15:15
L4	56	(US-20020063311-\$ or US-20020084513-\$ or US-20030141571-\$).did. or (US-3648131-\$ or US-4097890-\$ or US-4394712-\$ or US-4499655-\$ or US-4613891-\$ or US-4807021-\$ or US-4842699-\$ or US-4893174-\$ or US-4897708-\$ or US-4961833-\$ or US-5056216-\$ or US-5122856-\$ or US-5229647-\$ or US-5343071-\$ or US-5362975-\$ or US-5399898-\$ or US-5408123-\$ or US-5432999-\$ or US-5438212-\$ or US-5618752-\$ or US-5646067-\$ or US-5682062-\$ or US-5737052-\$ or US-5843844-\$ or US-5905275-\$ or US-5973396-\$).did. or (US-6002177-\$ or US-6122187-\$ or US-6168969-\$ or US-6184060-\$ or US-6222276-\$ or US-6236115-\$ or US-6278181-\$ or US-6314013-\$ or US-6326689-\$ or US-6340839-\$ or US-6383837-\$ or US-6400008-\$ or US-6410431-\$ or US-6420209-\$ or US-6429096-\$ or US-6429509-\$ or US-6437387-\$ or US-6444576-\$ or US-6512292-\$ or US-6534874-\$ or US-6566232-\$ or US-6577011-\$ or US-6577013-\$ or US-6608371-\$ or US-6611002-\$ or US-6614095-\$ or US-6670269-\$).did.	US-PGPUB; USPAT	OR	ON	2005/02/19 15:15
L5	48286	(wafer die (semiconductor near substrate)) near4 (hole via vias)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2005/02/19 15:16

L6	40908	5 and (method process step)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2005/02/19 15:16
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